

1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors





Product data sheet

1. General description

Planar passivated four quadrant triac in a SOT78 plastic package intended for use in general purpose bidirectional switching and phase control applications.

2. Features and benefits

- High blocking voltage capability
- Less sensitive gate for improved noise immunity
- · Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants

3. Applications

- General purpose motor controls
- General purpose switching

4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DRM}	repetitive peak off- state voltage		-	-	600	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; <u>Fig. 4</u> ; <u>Fig. 5</u>	-	-	65	A
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 102 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	-	8	A
Static chara	acteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2+ G+};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-	5	35	mA
		$V_D = 12 V; I_T = 0.1 A; T2+ G-;$ $T_j = 25 °C; Fig. 7$	-	8	35	mA
		$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-	11	35	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 7</u>	-	30	70	mA





5. Pinning information

Table 2.	Table 2. Pinning information								
Pin	Symbol	Description	Simplified outline	Graphic symbol					
1	T1	main terminal 1	mb	T2					
2	T2	main terminal 2	$2 \circ 4$	sym051					
3	G	gate							
mb	Τ2	mounting base; main terminal 2							
			TO-220AB (SOT78)						

6. Ordering information

Type number	Package	e				
	Name	Description	Version			
BT137-600	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			
BT137-600/DG/L01	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			
BT137-600/L01	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

7. Limiting values

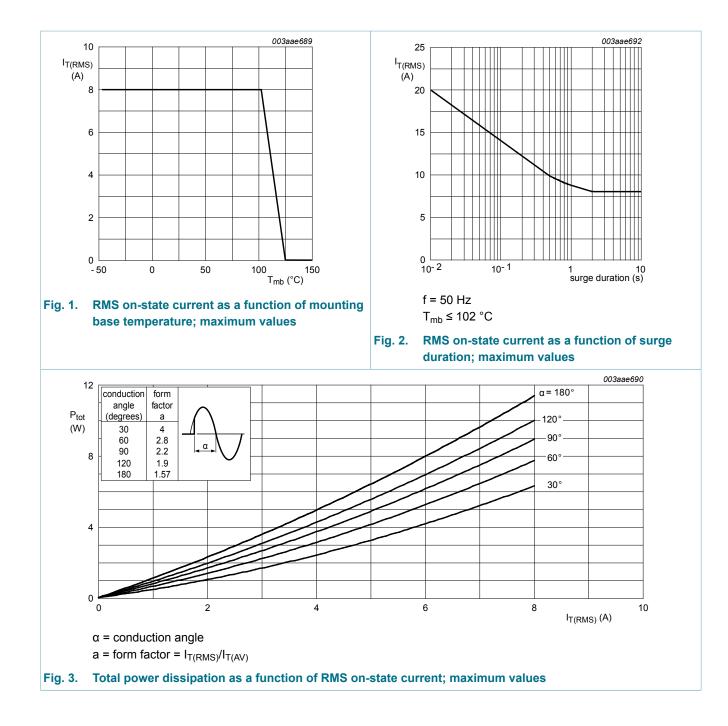
Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 102 \text{ °C}$; Fig. 1; Fig. 2; Fig. 3	-	8	A
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; <u>Fig. 4</u> ; <u>Fig. 5</u>	-	65	A
		full sine wave; $T_{j(init)} = 25 \text{ °C};$ t _p = 16.7 ms; <u>Fig. 4</u> ; <u>Fig. 5</u>	-	71	A
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	21	A ² s
dl _T /dt	rate of rise of on-state current	I_T = 12 A; I_G = 0.2 A; dI_G/dt = 0.2 A/µs; T2+ G+	-	50	A/µs
		I_T = 12 A; I_G = 0.2 A; dI_G/dt = 0.2 A/µs; T2+ G-	-	50	A/µs
		I_T = 12 A; I_G = 0.2 A; dI_G/dt = 0.2 A/µs; T2- G-	-	50	A/µs
		I_T = 12 A; I_G = 0.2 A; dI_G/dt = 0.2 A/µs; T2- G+	-	10	A/µs
I _{GM}	peak gate current		-	2	А
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

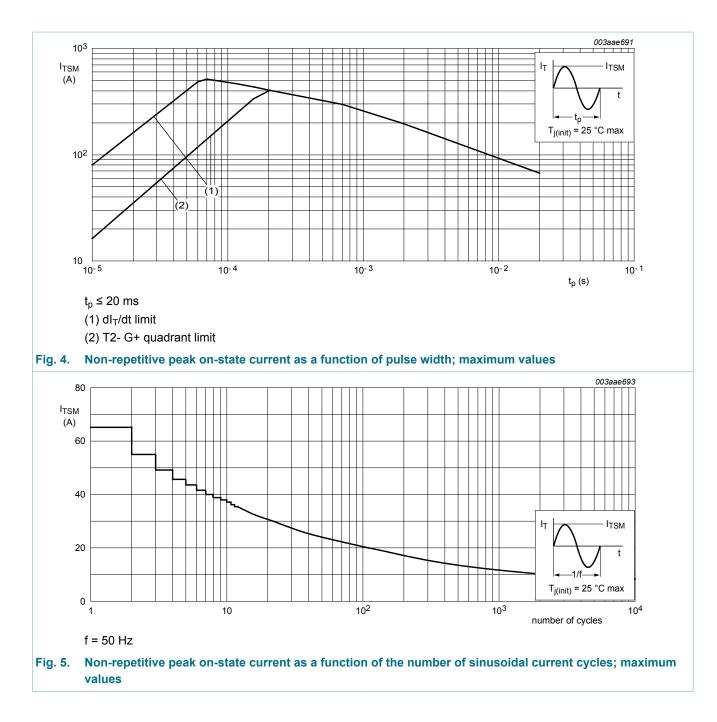
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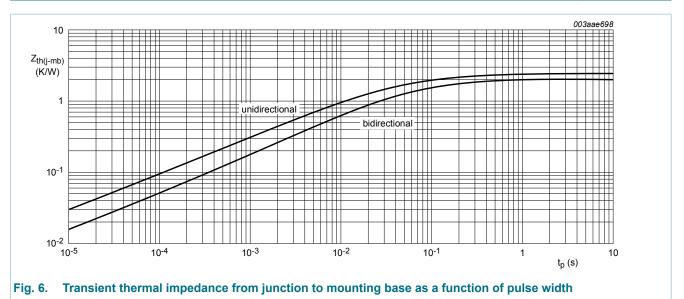
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8. Thermal characteristics

Table 5. 1	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	half cycle; <u>Fig. 6</u>	-	-	2.4	K/W
		full cycle; <u>Fig. 6</u>	-	-	2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W



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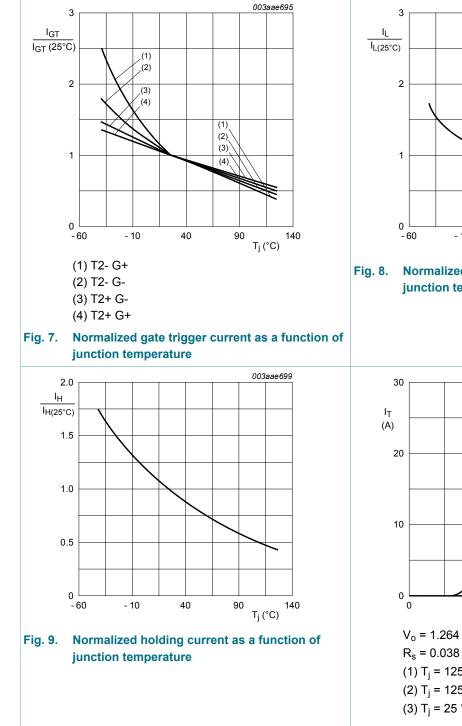
9. Characteristics

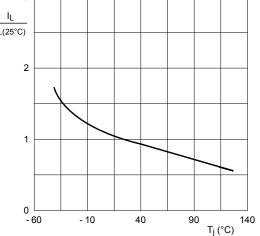
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics	I	I			
I _{GT}	gate trigger current	V_D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	-	5	35	mA
		V_D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 7	-	8	35	mA
		$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-	11	35	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 7</u>	-	30	70	mA
ΙL	latching current	V_D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 8</u>	-	7	30	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2+ G-};$ T _j = 25 °C; <u>Fig. 8</u>	-	16	45	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \text{ Fig. 8}$	-	5	30	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \text{ Fig. 8}$	-	7	45	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	5	20	mA
V _T	on-state voltage	I _T = 10 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.65	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic ch	aracteristics	· · · · · · · · · · · · · · · · · · ·	I			
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	100	250	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	V_D = 400 V; T_j = 95 °C; dI_{com}/dt = 3.6 A/ ms; I_T = 8 A; gate open circuit	-	20	-	V/µs
t _{gt}	gate-controlled turn-on time	I_{TM} = 12 A; V_D = 600 V; I_G = 0.1 A; dI_G/dt = 5 A/µs	-	2	-	μs

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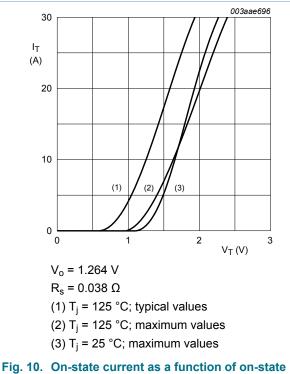
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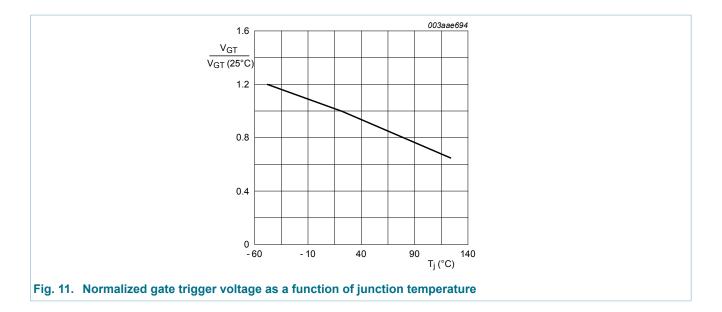




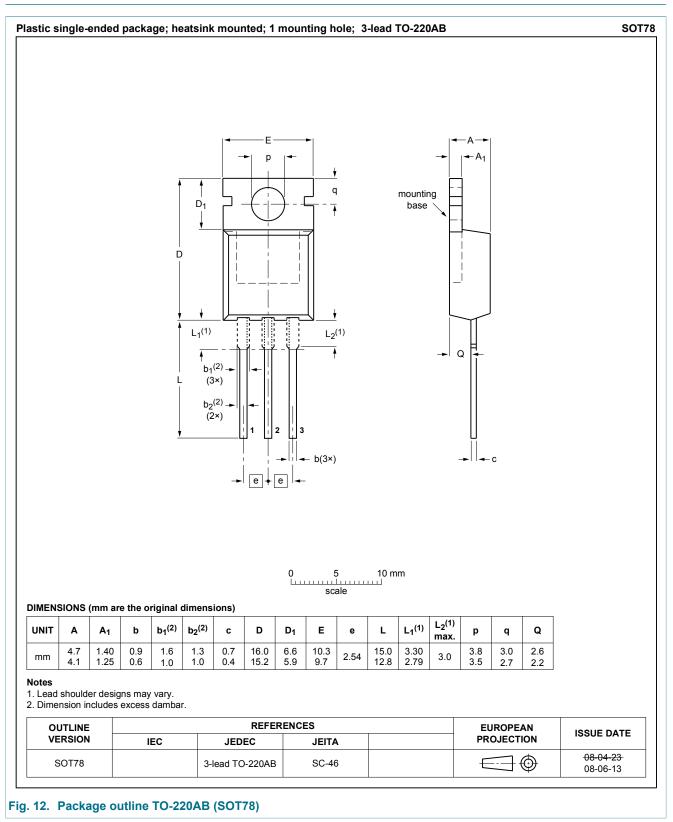
voltage

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10. Package outline



BT137-600

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11. Legal information

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

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